

# 國立臺灣師範大學 100 學年度碩士班招生考試試題

科目：電子學

適用系所：應用電子科技學系

注意：1.本試題共 4 頁，請依序在答案卷上作答，並標明題號，不必抄題。2.答案必須寫在指定作答區內，否則不予計分。

1. (20 points) Assume that  $v_i(t) = 10 \sin 2\pi t$ , V. Sketch and label the voltage transfer characteristics of the circuits shown in Fig. 1.

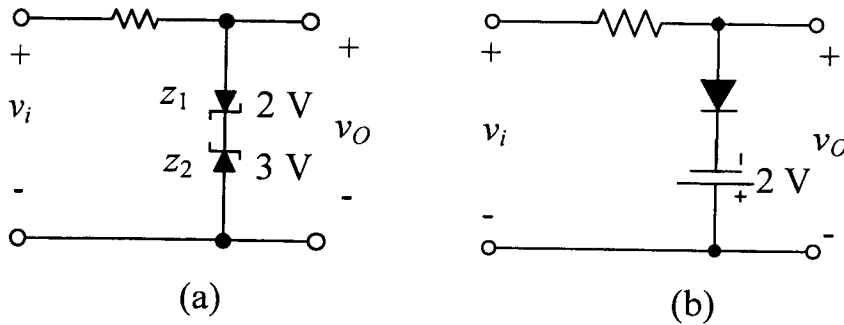


Fig. 1

2. (20 points) In the circuit of Fig. 2,  $v_{sig}$  is a small sine-wave signal with zero average. The transistor  $\beta$  is 100 and  $V_{BE}$  is 0.7 V.

- (a) Find  $R_E$  and  $R_C$  to establish a dc emitter current  $I_E = 0.5$  mA and a dc collector voltage  $V_C = +5$  V.
- (b) For the transistor  $r_o = 20$  k $\Omega$ , draw the small-signal equivalent circuit of the amplifier and find the voltage gain  $v_o/v_{sig}$ .

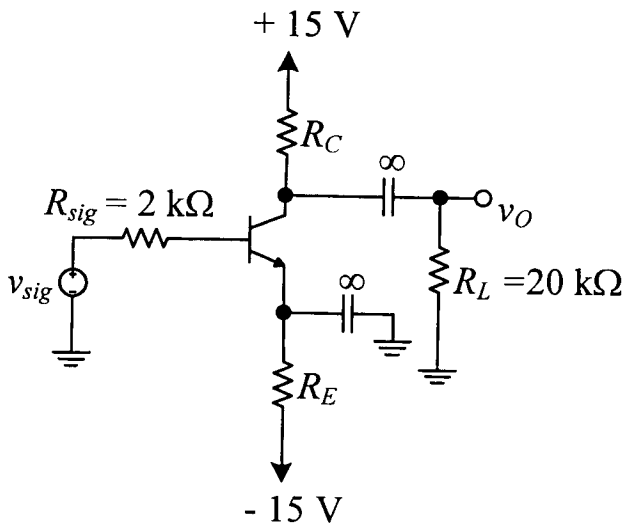


Fig. 2

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3. (10 points) Figure 3 shows a Miller integrator. If the integrator capacitor is shunted by a resistor  $R_F$ , how will the transfer function be modified? How will the frequency of the integrator pole be changed?

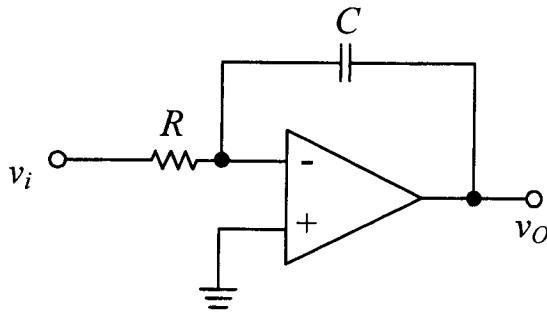


Fig. 3

4. (20 points) Consider the two-stage CMOS opamp in Fig. 4 with the following device geometries (in  $\mu\text{m}$ ).

Transistor	$Q_1$	$Q_2$	$Q_3$	$Q_4$	$Q_5$	$Q_6$	$Q_7$	$Q_8$
$W/L$	20/0.2	20/0.2	6.25/1	6.25/1	100/2	25/1	100/1	100/2

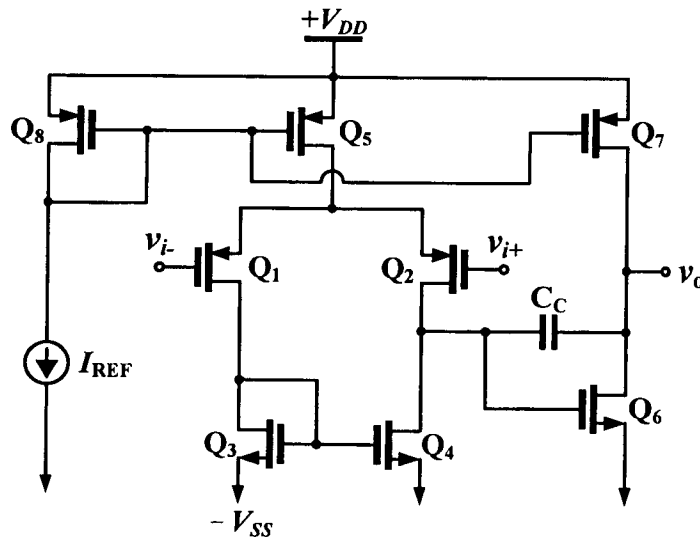


Fig. 4

Let  $I_{REF} = 90 \mu\text{A}$ ,  $V_{tn} = 0.45 \text{ V}$ ,  $V_{tp} = -0.45 \text{ V}$ ,  $\mu_n C_{ox} = 400 \mu\text{A/V}^2$ ,  $\mu_p C_{ox} = 100 \mu\text{A/V}^2$ ,  $V_{DD} = 1.8 \text{ V}$ ,  $V_{SS} = 0 \text{ V}$ , and  $|V_A| = 10 \text{ V}$ .

- (a) For devices  $Q_2$ , and  $Q_6$ , evaluate  $I_D$ ,  $|V_{GS}|$ ,  $g_m$ , and  $r_o$ . Neglect the effect of  $V_A$

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on all bias currents.

(b) Find the overall dc open-loop voltage gain  $A = v_o / (v_{i+} - v_{i-})$ .

(c) Also find the input common-mode range, and the output voltage range.

(d) What are the slew rate and unity-gain frequency of this opamp if  $C_C = 1.6$  pF?

5. (20 points) A voltage-to-current converter employing series-series feedback via resistor  $R_F$ . The p-channel MOSFETs,  $Q_3$  and  $Q_4$ , have the same dimension (W/L), and the n-channel MOSFETs have the dimension (W/L) shown in Fig. 5. Now, all MOSFETs are operated in saturation region and  $\mu_n C_{ox} = 20 \mu\text{A}/\text{V}^2$ ,  $|V_t| = 1$  V,  $|V_A| = 100$  V for all MOSFETs.

(a) What is the value of  $I_o/V_s$  obtained for large loop gain?

(b) Use feedback analysis to find a more exact value for  $I_o/V_s$ .

(c) If the output voltage is taken at the source of  $Q_5$ , what closed-loop voltage gain is realized?

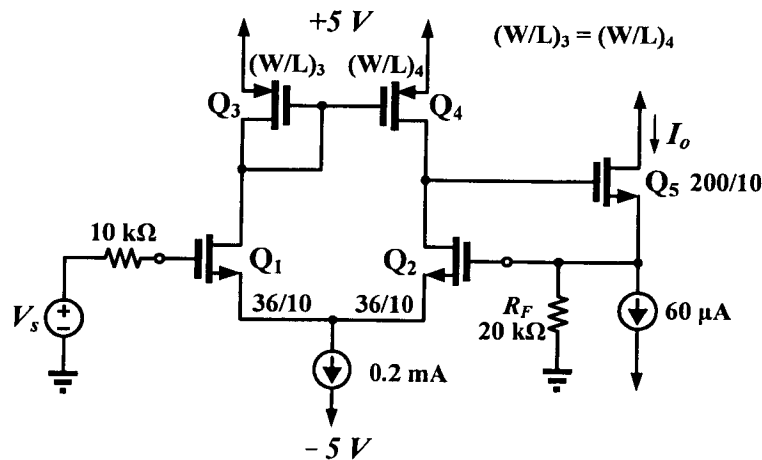


Fig. 5

6. (10 points) Consider a wideband low-gain amplifier stage, as shown in Fig. 6(a).

Transistors  $Q_1$  and  $Q_2$  have the same threshold voltage  $V_t$ , the same channel length  $L$  but different widths  $W_1$  and  $W_2$ . They are biased at the same  $V_{GS}$  and have the

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same unity-gain bandwidth  $\omega_T$ . Use the MOSFET equivalent circuit of Fig. 6(b) to model this amplifier stage assuming that its output is connecting to the input of an identical stage. Prove that the voltage gain  $V_o/V_i$  is

$$\frac{V_o}{V_i} = \frac{-g_{m1}/g_{m2}}{1 + \frac{s}{\omega_T / (1 + \frac{g_{m1}}{g_{m2}})}}$$

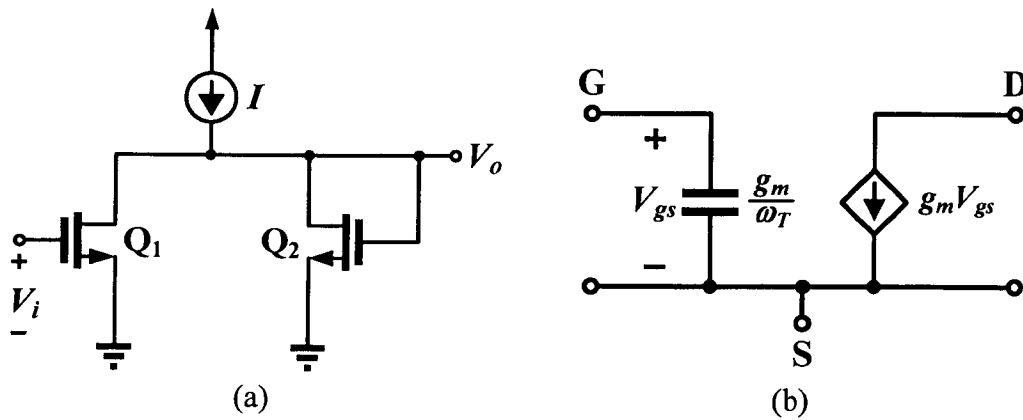


Fig. 6.